

POSTER SESSION THURSDAY

	Last Name	First Name	Laboratory	Country	Title
Th.1	Bollier	Isabelle	IBM Research	Switzerland	Electrical resistivity of hexagonal silicon germanium
Th.2	Ferrand	David	CNRS-Institut Néel	France	Light hole states in a strained quantum dot
Th.3	Gächter	Nadine	University of Basel	Switzerland	Optical properties related to novel inclined twin defects in InP [100] nanowires
Th.4	Gächter	Nadine	University of Basel	Switzerland	Giant bandgap tuning in 3-5 nanowires by post-growth hydrogen irradiation
Th.5	Gómez	Mikel	Paul-Drude-Institut	Germany	Composition and optical properties of group-III-assisted (In,Ga)As nanowires grown by molecular beam epitaxy
Th.6	Häuser	Patrick	University Duisburg-Essen	Germany	Improving the AlN transfer resistance by ex situ annealing for GaN on Silicon nanowire devices
Th.7	Jash	Asmita	Lund University	Sweden	Time-resolved photoluminescence studies of single interface wurtzite/zincblende heterostructured InP nanowires
Th.8	Kaur	Yashpreet	University of Basel	Switzerland	Thermal rectification in telescopic nanowires
Th.9	Mosahebfard	Zohreh	Universität Siegen	Germany	The impact of nanomechanical stress and electrical current on the structure of individual GaAs nanowires
Th.10	Granger	Francis	Univ. Grenoble Alpes	France	Radiation pattern of CdSe quantum dot in a taper-shaped ZnSe nanowire
Th.11	van Tilburg	Marvin	Eindhoven Univ. Technology	Netherlands	First Stimulated Emission from Silicon Nanowires
Th.12	Böckle	Raphael	TU Wien	Austria	Bias-Switchable Photoconductance in a Nanoscale Ge Photodetector Operated in the Negative Differential Resistance Regime
Th.13	Ciostek	Czcibor	University of Wuerzburg	Germany	Periodic magnetoconductance oscillations in core-multishell HgTe nanowires
Th.14	Daudin	Bruno	CEA Grenoble	France	Heterogeneous electrical dopant distribution in GaN nanowires
Th.15	Fust	Sergej	Walter Schottky Institut	Germany	Transport properties of novel InAs-AlSb core-shell nanowire FETs
Th.16	van de Sande	Vince	Eindhoven Univ. Technology	Netherlands	Towards gate-tunable topological crystalline insulator devices based on PbSnTe nanowires
Th.17	De Carlo	Ivan	Politecnico di Torino	Italy	Nb nanostripes-based devices for the visualization of the 2D \u2013 1D crossover in low temperature superconductors
Th.18	Debbarma	Rousan	Politecnico di Torino	Italy	Effects of parity and symmetry on the Aharonov-Bohm phase of a quantum ring
Th.19	Grove-Rasmussen	Kasper	University of Copenhagen	Danemark	Towards quantum dot-superconducting island chains in Al/InAs nanowires
Th.20	Sestoft	Joachim E.	University of Copenhagen	Danemark	Cross-sectioned nanowires: a scalable platform for nanocrystal-based quantum electronics
Th.21	Spies	Maria	Nanoscience Institute CNR	Italy	Investigation of superconductor-semiconductor hybrid structures in the Al-InAs system fabricated with the solid-state diffusion technique
Th.22	Gloriès	Henri-Gabriel	Lyon Inst. of Nanotechnology	France	Optical properties of hybrid structures based on ferroelectric polymers and III-V nanowires grown on silicon substrate
Th.23	Davtyan	Rubina	Lund University	Sweden	Image analysis pipeline for improving the limit of the detection of light guiding GaP nanowires
Th.24	Bochicchio	Emanuele	Eindhoven Univ. Technology	Netherlands	Ultimate limit InP nanowire solar cells
Th.25	Leonetti	Giuseppe	Politecnico di Torino	Italy	Niobium nanowire fabrication through electromigration in resistive switching cells
Th.26	Potocnik	Teja	University of Cambridge	United Kingdom	Automated, computer-vision enabled fabrication of nanowire devices
Th.27	Schreitmüller	Tobias	Walter Schottky Institut	Germany	Optoelectronic properties of GaAs(Sb)-AlGaAs core-shell NW diodes on silicon
Th.28	Vitale	Francesco	Universität Jena	Germany	Temperature-dependent lasing operation of hybrid semiconductor nanowire - metal grating plasmonic nanolasers
Th.29	Dursap	Thomas	Lyon Inst. of Nanotechnology	France	III- V core / oxide shell nanowires for light - driven water splitting
Th.30	Wang	Chaoqi	CNRS Laboratoire PICM	France	Triple radial junction silicon nanowire solar cells with 2.2 V open circuit voltage
Th.31	Adham	Kristi	Lund University	Sweden	Growth of branched nanowires via solution based Au deposition for next-generation light emitting diodes
Th.32	Al Hassan	Ali	Karlsruhe Inst. of Technology	Germany	Correlating the crystal phase of as-grown GaAs nanowires with the wetting angle of catalyst Ga droplets at their apex by GISAXS and asymmetric XRD
Th.33	Al Humaidi	Mahmoud	Karlsruhe Inst. of Technology	Germany	Impact of the substrate temperature on the shell growth and bending direction of core-shell nanowires
Th.34	Auzelle	Thomas	Paul-Drude-Institut	Germany	Density control of GaN nanowires at the wafer-scale using self-assembled Si patches on sputtered TiN 111
Th.35	Bermeo	Marie	Lund University	Sweden	Gallium phosphide nanowires seeded by palladium nanoparticles
Th.36	Cavalli	Alessandro	INL	Portugal	CuInSe2 Nanostructures for Solar Cells Applications
Th.37	Gómez-Palos	Isabel	IMDEA Materials	Spain	Ultrafast synthesis of SiC nanowires using floating catalyst
Th.38	Legardinier	Lisa	Grenoble INP LMGP	France	Tunable dimensions of ZnO nanowires grown by metal-organic chemical vapor deposition and its impact on the piezoelectric properties
Th.39	Mientjes	Mathijs	Eindhoven Univ. Technology	Netherlands	Growth and electrical characterization of MBE grown self-catalyzed Pb1-xSnxTe nanowires with CdTe shell
Th.40	Nagda	Gunjan Piyush	University of Copenhagen	Danemark	Selective area growth of InAs nanowires on GaAs(311)A substrates
Th.41	Rossi	Marco	Eindhoven Univ. Technology	Netherlands	Bottom-up growth of InSb nanoflakes via nanoscale-controlled nanowire collisions
Th.42	Semlali	Elias	Univ. Clermont- Institut Pascal	France	Selective area growth of InGaN nanowires by HVPE for LEDs application
Th.43	Song	Man Suk	Weizmann Institute	Israël	Incorporation of Eu in InAs nanowire growth by MBE
Th.44	Zytkiewicz	Zbigniew R.	Polish Academy of Sciences	Poland	On the origin of enhanced GaN NW formation on a-AlxOy buffers by PAMBE
Th.45	Andersen	Christopher Røhl	Technical Univ. of Denmark	Danemark	Surface tension of Au-catalysed GaAs nanowires
Th.46	Vettori	Marco	Eindhoven Univ. Technology	Netherlands	Critical lengths for the onset of polytypism in MOVPE-grown GaAs nanowires
Th.47	del Giudice	Fabio	Technical University of Munich	Germany	Epitaxial type-I and type-II InAs-AlAsSb core-shell nanowires on silicon
Th.48	Marin	Francisca	Paul-Drude-Institut	Germany	Effect of bending on the photoluminescence of GaAs nanowires with a low degree of polytypism
Th.49	Valera	Lucie	Univ. Grenoble Alpes	France	Core-shell GaN/Al(Ga)N heterostructures: from quantum wells for UV-A to monolayers for UV-C
Th.50	Zannier	Valentina	Nanoscience Institute CNR	Italy	Selective-area epitaxy of InGaAsP buffer multilayer for in-plane InAs nanowire integration
Th.51	Dieulesaint	Alexandre	Grenoble INP LMGP	France	Engineering of defect complexes in ZnO nanowires grown by chemical bath deposition using oxygen plasma treatment
Th.52	Irish	Austin	Lund University	Sweden	Cross-sectional Surface Potential Microscopy for in-situ Characterization of Photovoltaic Nanowire Arrays